To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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3SK297

Silicon N-Channel Dual Gate MOS FET

ADE-208-389A (Z)
2nd. Edition
Mar. 2001

Application

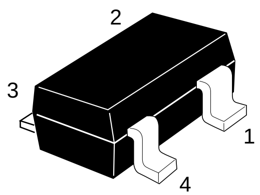
UHF / VHF RF amplifier

Features

- Low noise figure.
  NF = 1.0 dB typ. at f = 200 MHz
- Capable of low voltage operation

Outline

MPAK-4



1. Source
2. Gate1
3. Gate2
4. Drain

Note: Marking is "ZP–"

Attention: This device is very sensitive to electro static discharge.
It is recommended to adopt appropriate cautions when handling this transistor.

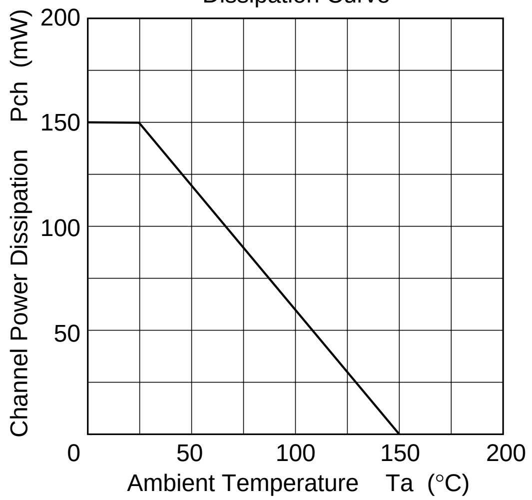
Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	12	V
Gate 1 to source voltage	V_{G1S}	±8	V
Gate 2 to source voltage	V_{G2S}	±8	V
Drain current	I_D	25	mA
Channel power dissipation	Pch	150	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

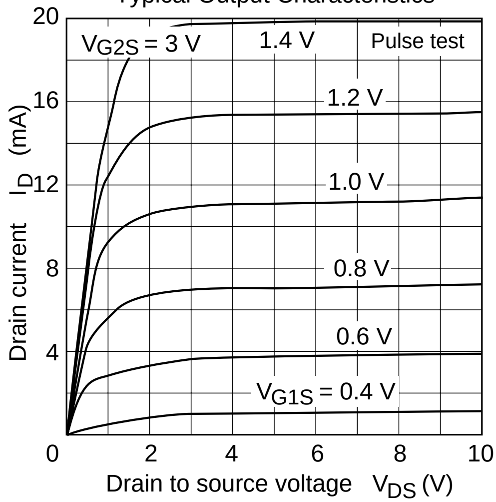
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSX}$	12	—	—	V	I_D = 200 µA , V_{G1S} = –3 V, V_{G2S} = –3 V
Gate 1 to source breakdown voltage	$V_{(BR)G1SS}$	±8	—	—	V	I_{G1} = ±10 µA, V_{G2S} = V_{DS} = 0
Gate 2 to source breakdown voltage	$V_{(BR)\ G2SS}$	±8	—	—	V	I_{G2} = ±10 µA, V_{G1S} = V_{DS} = 0
Gate 1 cutoff current	I_{G1SS}	—	—	±100	nA	V_{G1S} = ±6 V, V_{G2S} = V_{DS} = 0
Gate 2 cutoff current	I_{G2SS}	—	—	±100	nA	V_{G2S} = ±6 V, V_{G1S} = V_{DS} = 0
Drain current	$I_{DS(on)}$	0.5	—	10	mA	V_{DS} = 6 V, V_{G1S} = 0.75V, V_{G2S} = 3 V
Gate 1 to source cutoff voltage	$V_{G1S(off)}$	0	—	+1.0	V	V_{DS} = 10 V, V_{G2S} = 3V, I_D = 100 µA
Gate 2 to source cutoff voltage	$V_{G2S(off)}$	0	—	+1.0	V	V_{DS} = 10 V, V_{G1S} = 3V, I_D = 100 µA
Forward transfer admittance	$\|y_{fs}\|$	16	20	—	mS	V_{DS} = 6 V, V_{G2S} = 3V, I_D = 10 mA, f = 1 kHz
Input capacitance	Ciss	2.4	2.9	3.4	pF	V_{DS} = 6 V, V_{G2S} = 3V, I_D = 10 mA, f = 1 MHz
Output capacitance	Coss	0.8	1.0	1.4	pF	
Reverse transfer capacitance	Crss	—	0.023	0.04	pF	
Power gain	PG	22	25	—	dB	V_{DS} = 6 V, V_{G2S} = 3V, I_D = 10 mA, f = 200 MHz
Noise figure	NF	—	1.0	1.8	dB	
Power gain	PG	12	15	—	dB	V_{DS} = 6 V, V_{G2S} = 3V, I_D = 10 mA, f = 900 MHz
Noise figure	NF	—	3.2	4.5	dB	
Noise figure	NF	—	2.8	3.5	dB	V_{DS} = 6 V, V_{G2S} = 3V, I_D = 10 mA, f = 60 MHz

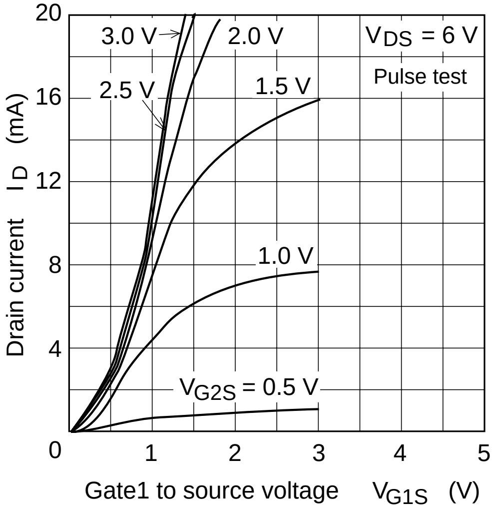
Maximum Channel Power Dissipation Curve



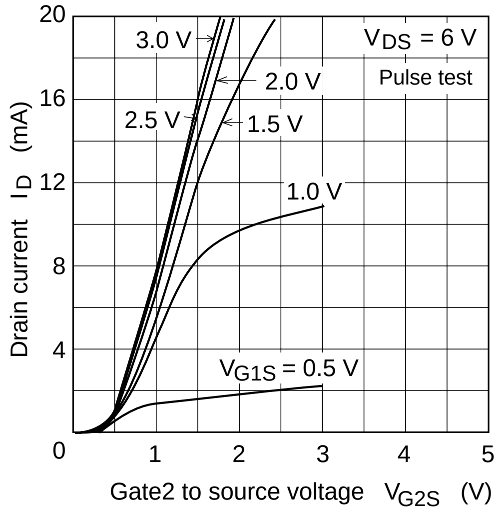
Typical Output Characteristics



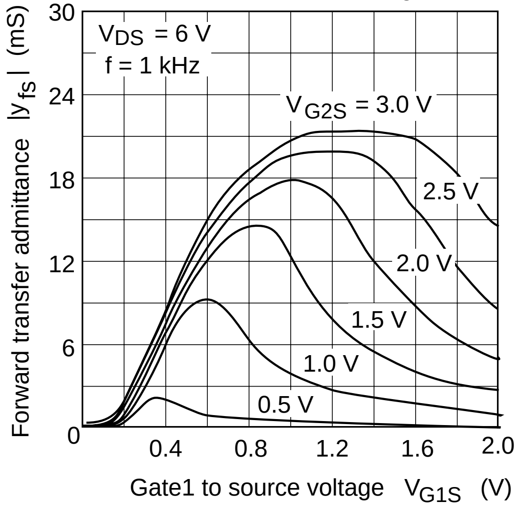
Drain Current vs. Gate1 to Source Voltage



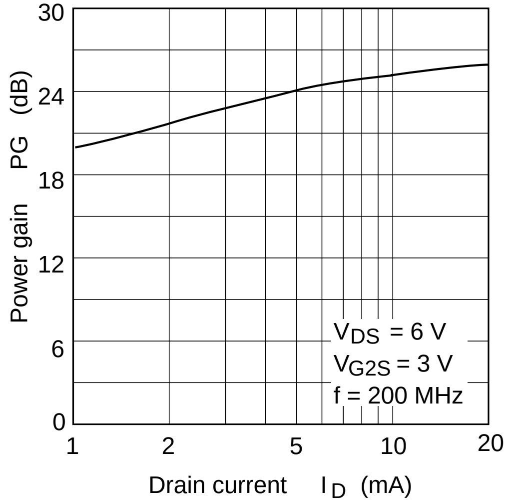
Drain Current vs. Gate2 to Source Voltage



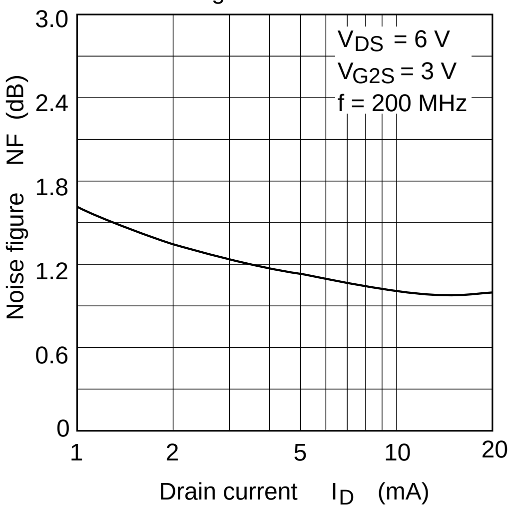
Forward Transfer Admittance vs. Gate1 to Source Voltage



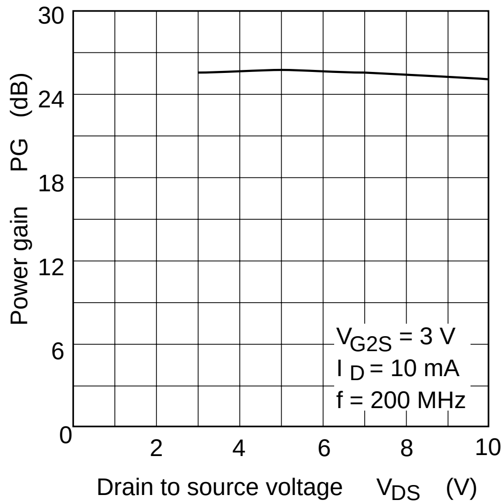
Power Gain vs. Drain Current



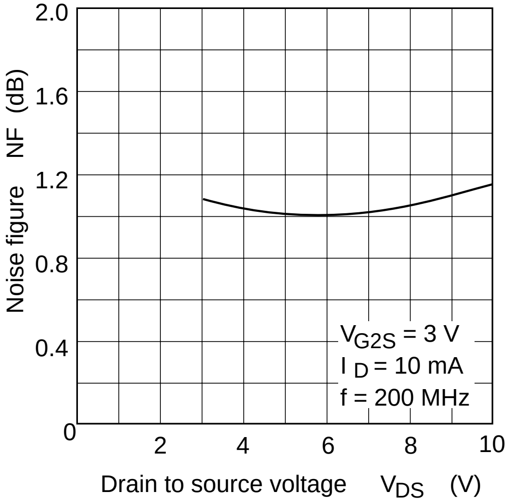
Noise Figure vs. Drain Current



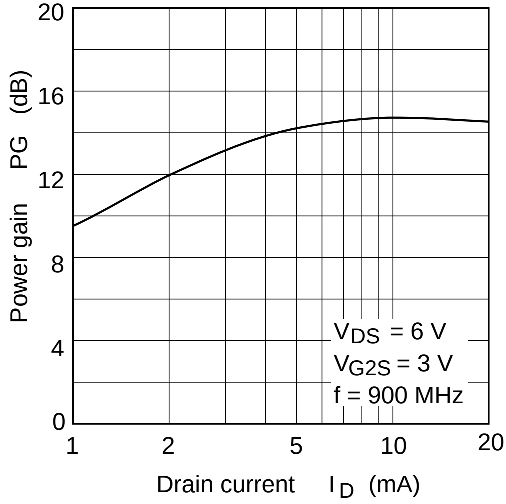
Power Gain vs. Drain to Source Voltage



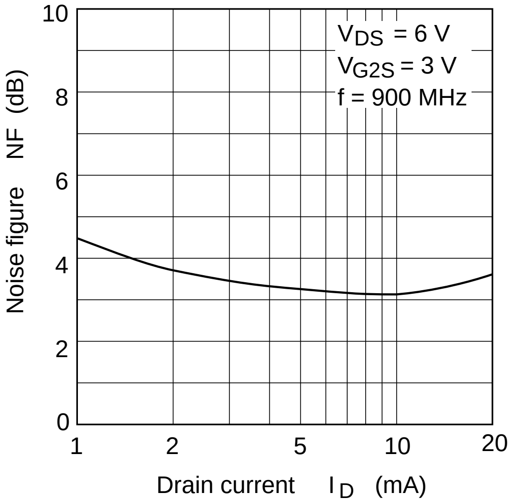
Noise Figure vs. Drain to Source Voltage



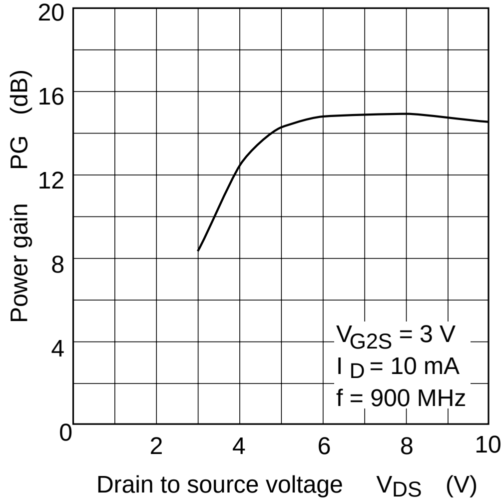
Power Gain vs. Drain Current

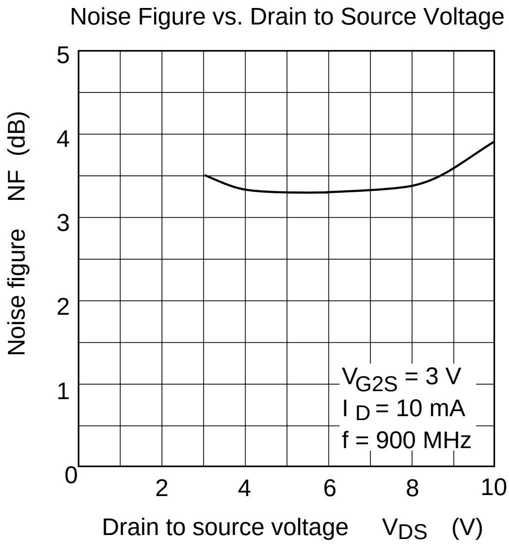


Noise Figure vs. Drain Current

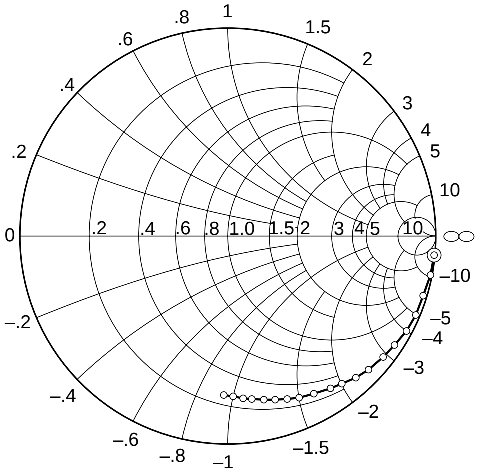


Power Gain vs. Drain to Source Voltage



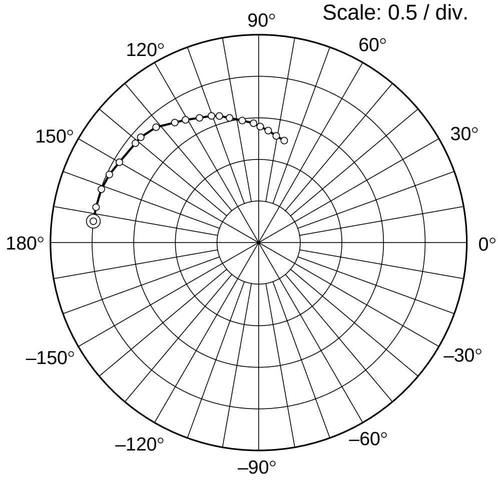

Noise Figure vs. Drain to Source Voltage
Noise figure NF (dB)
5
4
3
2
1
0
2
4
6
8
10
V_{G2S} = 3 V
I_D = 10 mA
f = 900 MHz
Drain to source voltage V_{DS} (V)

S11 Parameter vs. Frequency



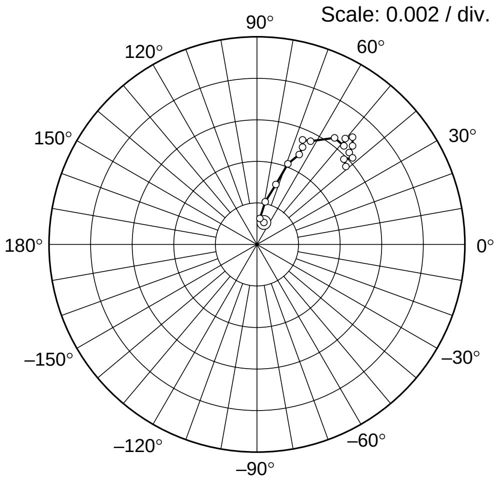
Condition: V_{DS} = 6 V , V_{G2S} = 3 V
I_D = 10 mA , Zo = 50 Ω
50 to 1000 MHz (50 MHz step)

S21 Parameter vs. Frequency



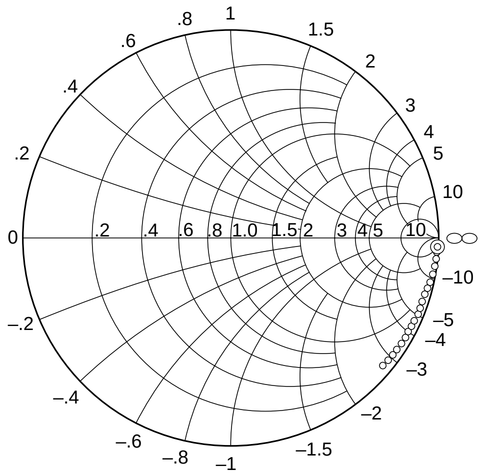
Condition: V_{DS} = 6 V , V_{G2S} = 3 V
I_D = 10 mA , Zo = 50 Ω
50 to 1000 MHz (50 MHz step)

S12 Parameter vs. Frequency



Condition: V_{DS} = 6 V , V_{G2S} = 3 V
I_D = 10 mA , Zo = 50 Ω
50 to 1000 MHz (50 MHz step)

S22 Parameter vs. Frequency



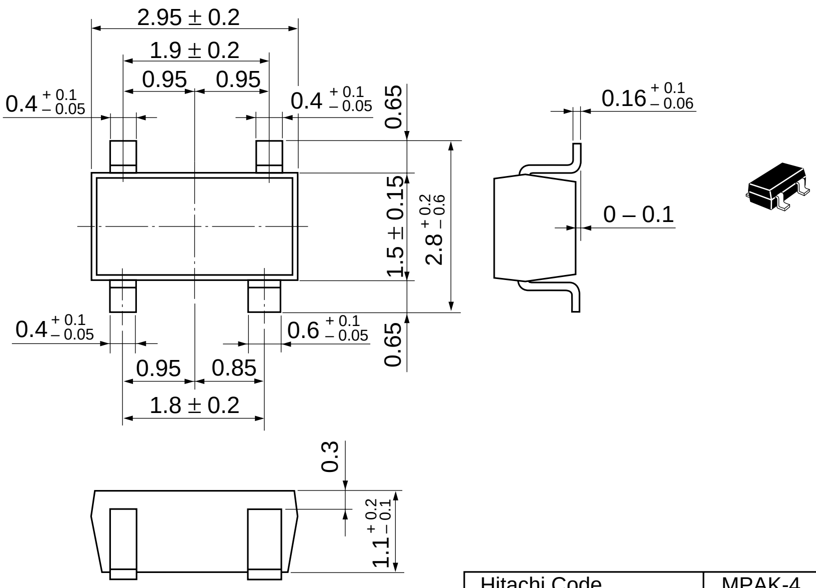
Condition: V_{DS} = 6 V , V_{G2S} = 3 V
I_D = 10 mA , Zo = 50 Ω
50 to 1000 MHz (50 MHz step)

S Parameter (V$_{DS}$ = 6 V, V$_{G2S}$ = 3 V, I$_{D}$ = 10 mA, Z$_{O}$ = 50)

Freq.	S11		S21		S12		S22	
(MHz)	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
50	0.994	–5.8	2.04	173.6	0.00116	76.9	0.993	–2.2
100	0.993	–11.0	2.02	167.4	0.00132	85.7	0.993	–4.5
150	0.986	–16.8	2.00	161.5	0.00229	78.2	0.991	–6.4
200	0.980	–22.5	1.98	155.5	0.00313	73.5	0.990	–8.5
250	0.973	–27.8	1.94	149.6	0.00427	68.7	0.987	–10.5
300	0.950	–33.0	1.90	142.6	0.00473	63.9	0.985	–12.5
350	0.936	–38.3	1.86	137.1	0.00536	64.3	0.982	–14.4
400	0.924	–43.4	1.83	131.6	0.00561	64.5	0.979	–16.2
450	0.912	–48.0	1.77	126.8	0.00562	60.9	0.975	–18.2
500	0.893	–52.5	1.71	121.0	0.00640	53.5	0.971	–20.2
550	0.874	–57.3	1.67	115.5	0.00638	49.3	0.967	–22.0
600	0.859	–62.0	1.64	111.1	0.00647	49.0	0.964	–23.9
650	0.846	–66.1	1.58	106.7	0.00667	50.2	0.960	–25.8
700	0.829	–69.8	1.50	102.1	0.00694	49.3	0.955	–27.6
750	0.810	–74.2	1.46	97.1	0.00661	46.6	0.952	–29.4
800	0.802	–78.0	1.44	92.7	0.00618	43.7	0.948	–31.2
850	0.791	–81.6	1.38	88.9	0.00622	44.7	0.944	–33.2
900	0.778	–84.6	1.34	84.2	0.00615	43.6	0.940	–35.1
950	0.756	–88.5	1.30	80.2	0.00576	45.1	0.935	–36.8
1000	0.751	–92.2	1.26	75.9	0.00562	40.7	0.932	–38.5

Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	MPAK-4
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.013 g

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Hitachi, Ltd.
Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straβe 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel : <65>-538-6533/538-8577
Fax : <65>-538-6933/538-3877
URL : http://www.hitachi.com.sg

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel : <886>-(2)-2718-3666
Fax : <886>-(2)-2718-8180
Telex : 23222 HAS-TP
URL : http://www.hitachi.com.tw

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel : <852>-(2)-735-9218
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Colophon 2.0

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